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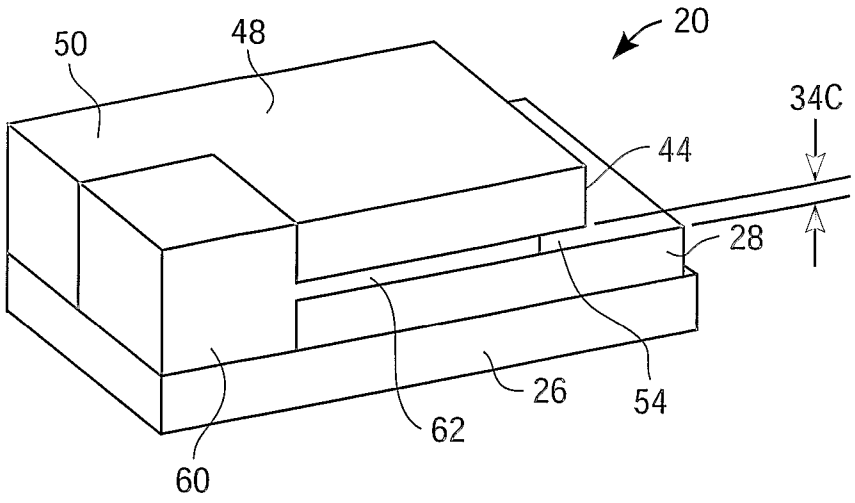
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(54) Title: A METHOD OF FORMING AN ELEMENT OF A MICROELECTRONIC CIRCUIT



(57) Abstract: A method is described for forming an element of a microelectronic circuit. A sacrificial layer is formed on an upper surface of a support layer. The sacrificial layer is extremely thin and uniform. A height-defining layer is then formed on the sacrificial layer, whereafter the sacrificial layer is etched away so that a well-defined gap is left-between an upper surface of the support layer and a lower surface of the height-defining layer. A monocrystalline semiconductor material is then selectively grown from a nucleation silicon site through the gap. The monocrystalline semiconductor material forms a monocrystalline layer having a thickness corresponding to the thickness of the original sacrificial layer.

WO 2004/082002 A1